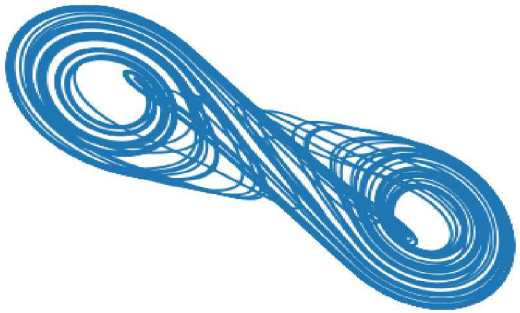
SAND2018-13455PE

Physical Unclonable Functions for Cryptographic Key Generation

Physics and Information Theoretic Considerations



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Sandia National Laboratories

Exceptional service in the national interest

U.S. DEPARTMENT OF ENERGY

NNSA National Nuclear Security Administration

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Keys: The Entropy Problem

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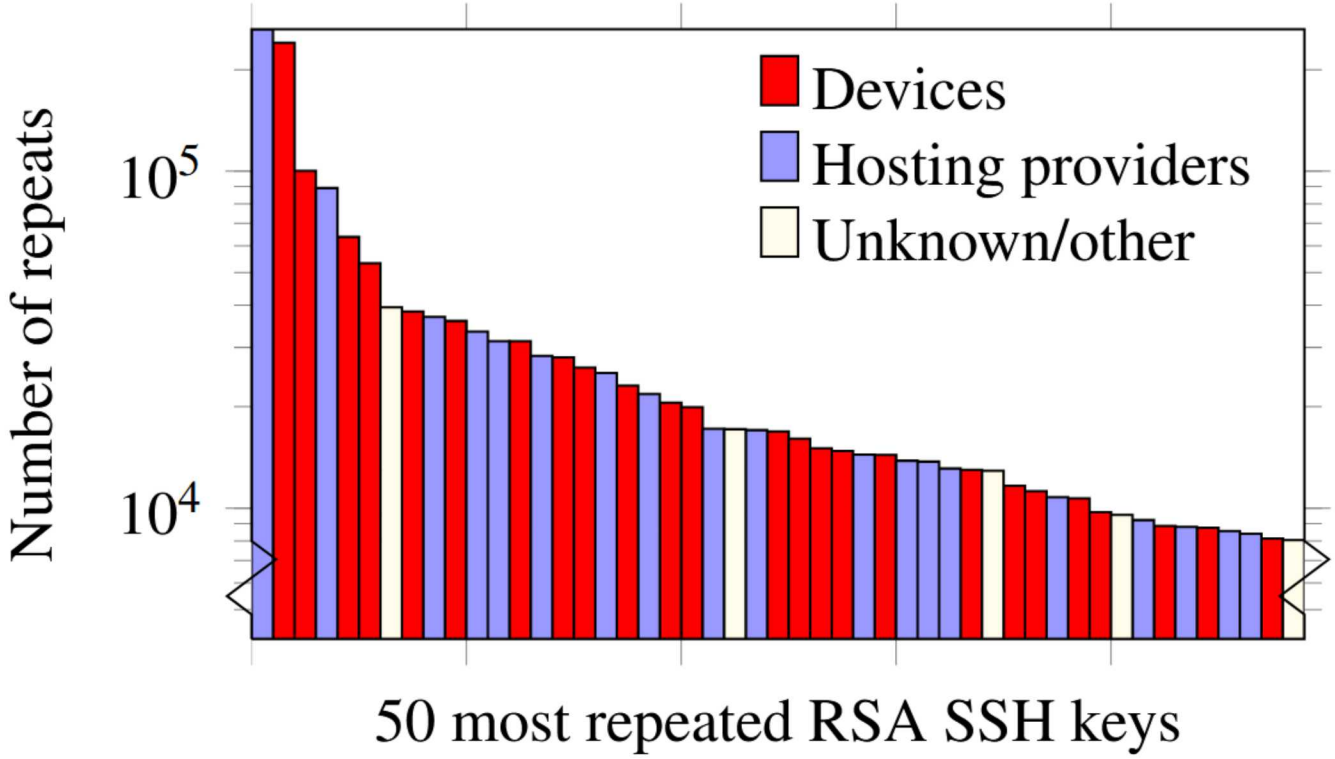
- Linux Random Number Generator (RNG): Failure in Entropy
  - Servers, IoT devices
  - Insufficient diversity of devices and environments → insufficient entropy
  - Weak/common TLS/SSH keys, usually generated on first boot



N Heninger, et al., "Mining Your Ps and Qs", USENIX (2012)

Keys: The Uniqueness Problem

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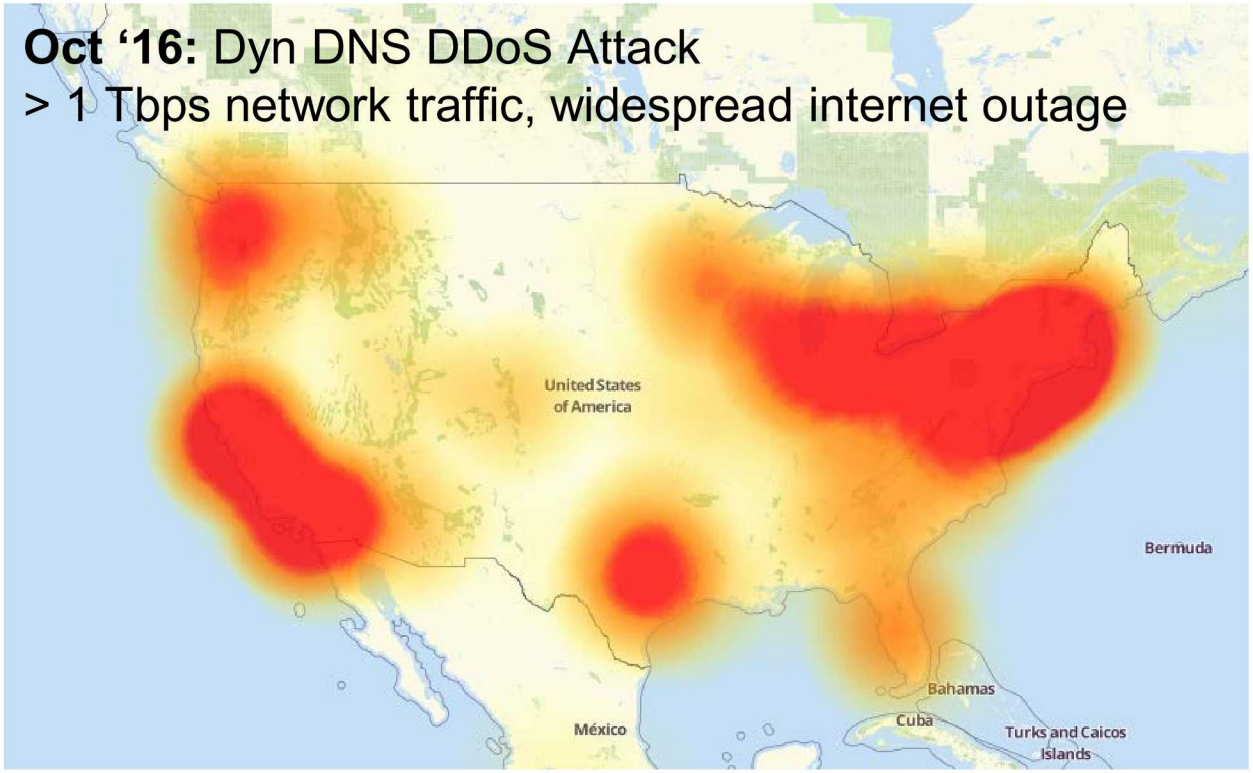
- Mirai Botnet: Failure in Identity and Key Management
  - Internet-of-Things (IoT) devices, i.e., routers, webcams
  - 60+ common default usernames (identities) and passwords (keys)
  - 600,000 devices hijacked for Distributed Denial of Service (DDoS) attacks




```
admin
administrator
root
user
<null>
…
```

```
password
1234
12345
admin
<null>
…
```

Keys: The Storage Problem

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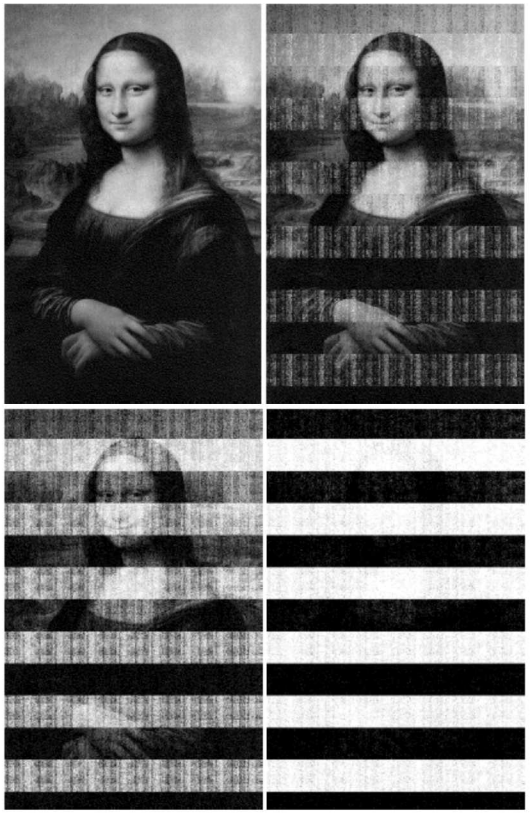
- Cold Boot Attack: Failure in Secure Key Storage
  - Dynamic Random Access Memory (DRAM)
  - Data retention extended from seconds to minutes by lowering temperature
  - Recovered AES, DES, and RSA keys stored in memory



A. Halderman, et al., “Cold Boot Attacks on Encryption Keys”, USENIX (2009)

Physical Unconable Functions (PUFs)

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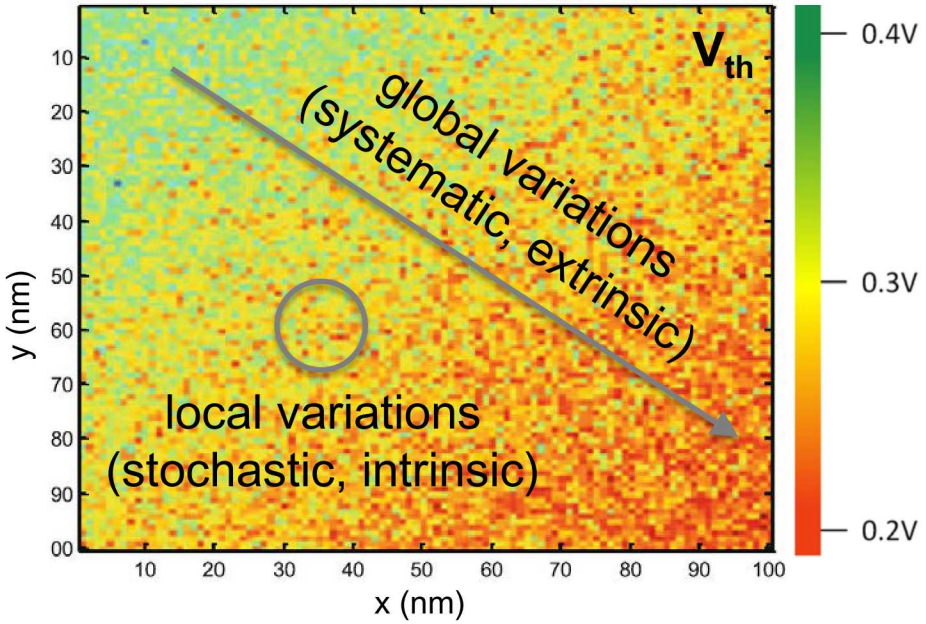
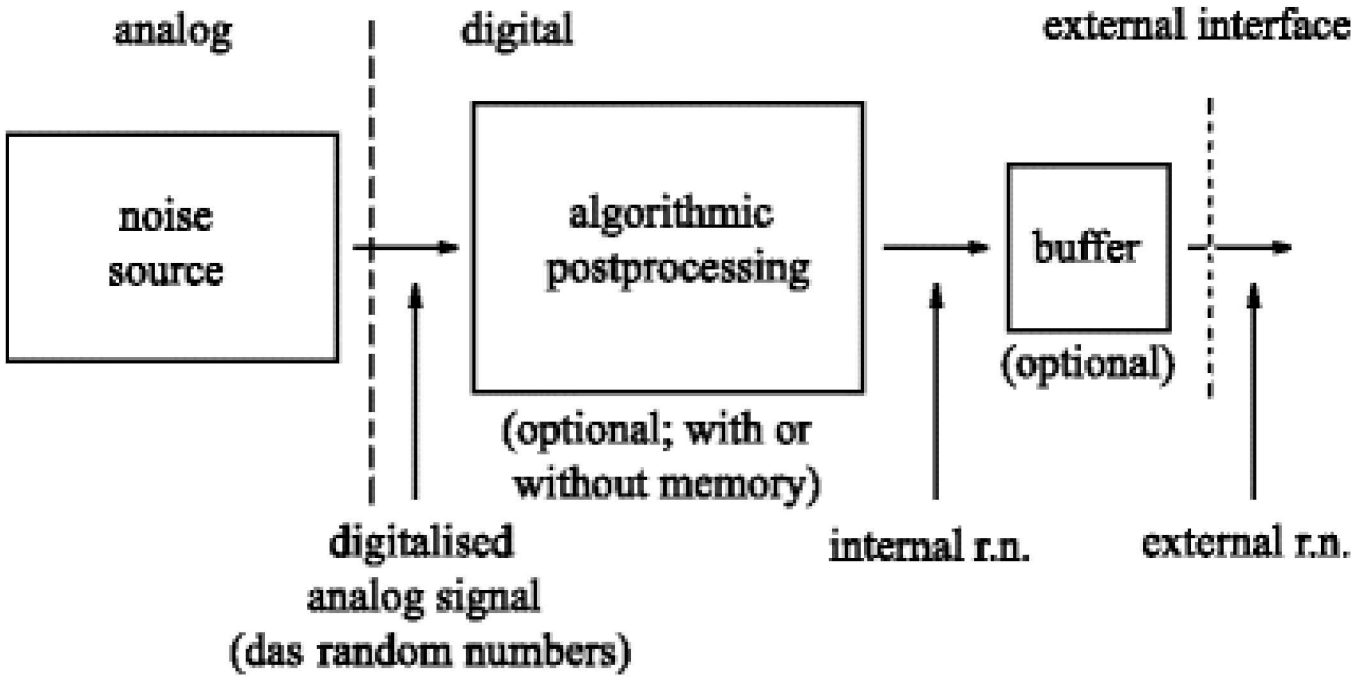
- Semiconductor, a.k.a. Integrated Circuit PUFs
  Proposed solution to key entropy / identity / storage problems
  - **Entropy:** Manufacturing variations in semiconductor materials, e.g., doping, oxide thickness, roughness
  - **Identity:** Capture these variations using semiconductor devices to form a digital fingerprint



- **Storage:** Keying material stored as intrinsic materials properties
  Keys dynamically generated on the fly, never stored in memory

Key Generation with PUFs

- Keys should be *n*-bits long depending on security requirements
- Keys should be independently, identically distributed (IID)
- Keys should remain the same throughout the duration of use



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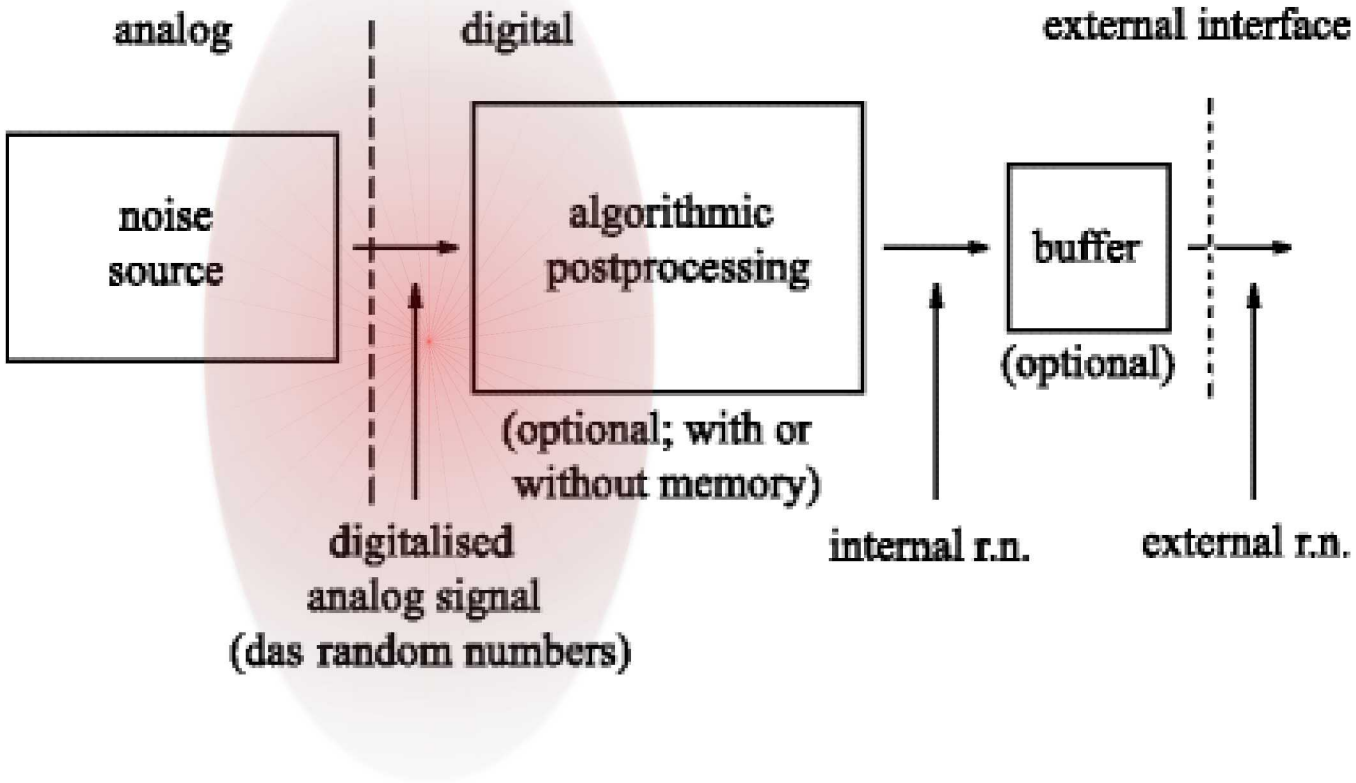
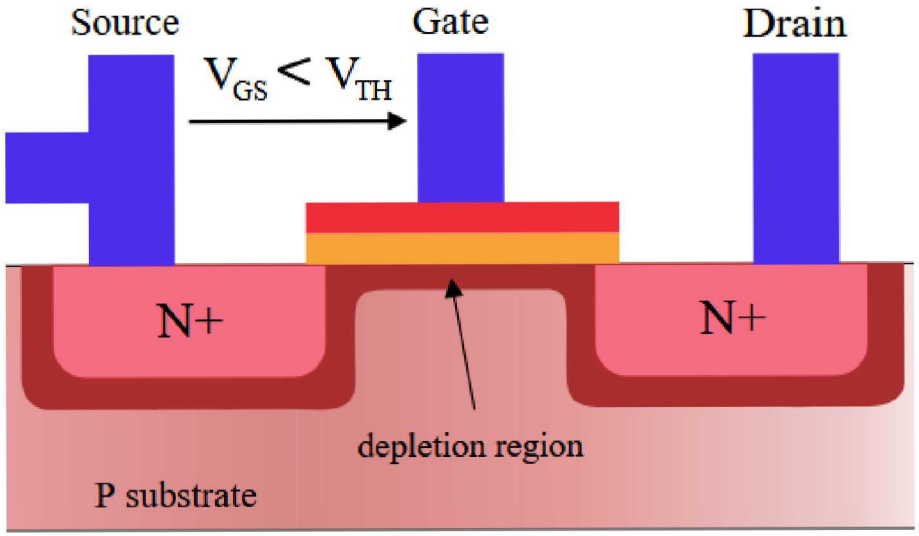
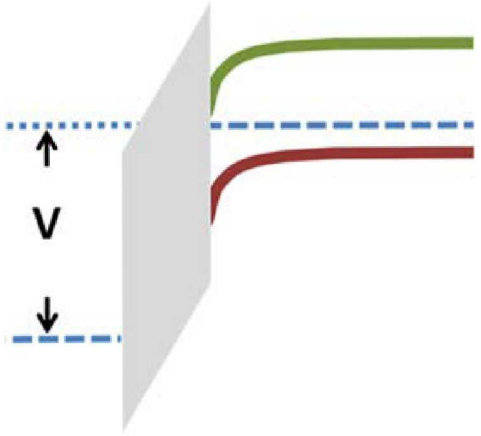


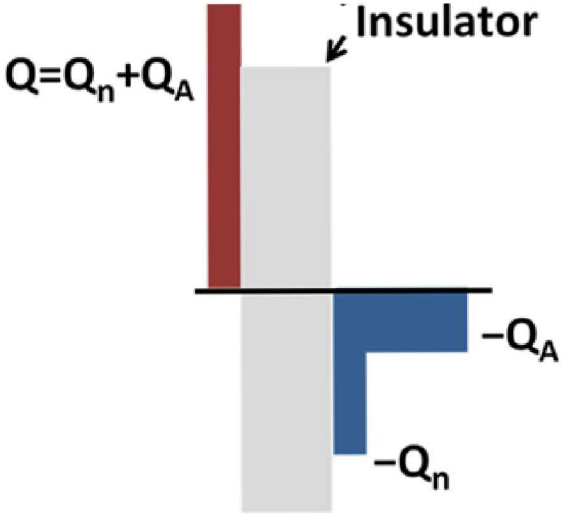
Integrated Circuit PUFs

- Metal-Oxide-Semiconductor (MOS) Transistor is the fundamental readout device in IC PUFs

nFET







$$I_D = \frac{\mu_n C_{ox}}{2} \frac{W}{L} [V_{GS} - V_{th}]^2 [1 + \lambda(V_{DS} - V_{DSsat})]$$

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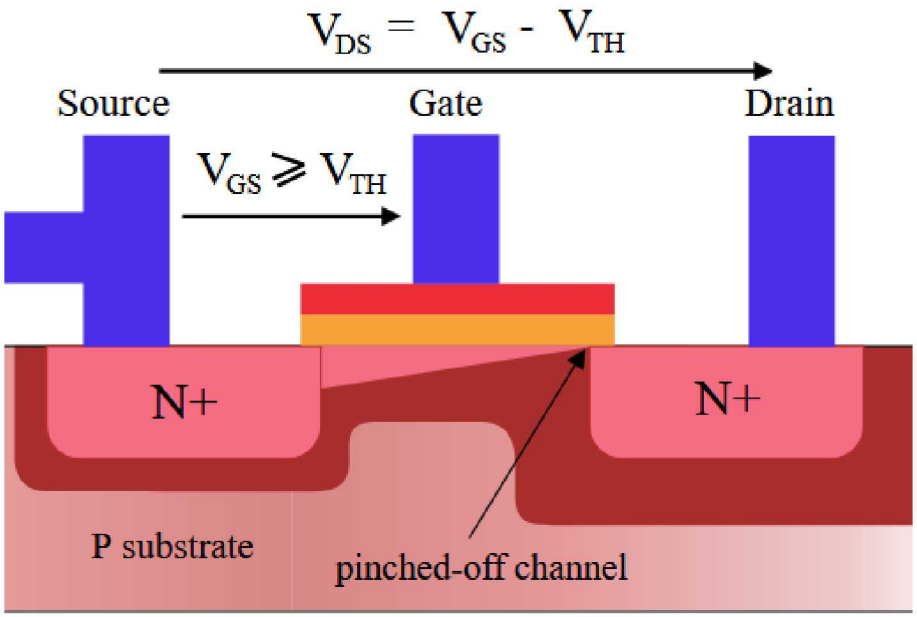

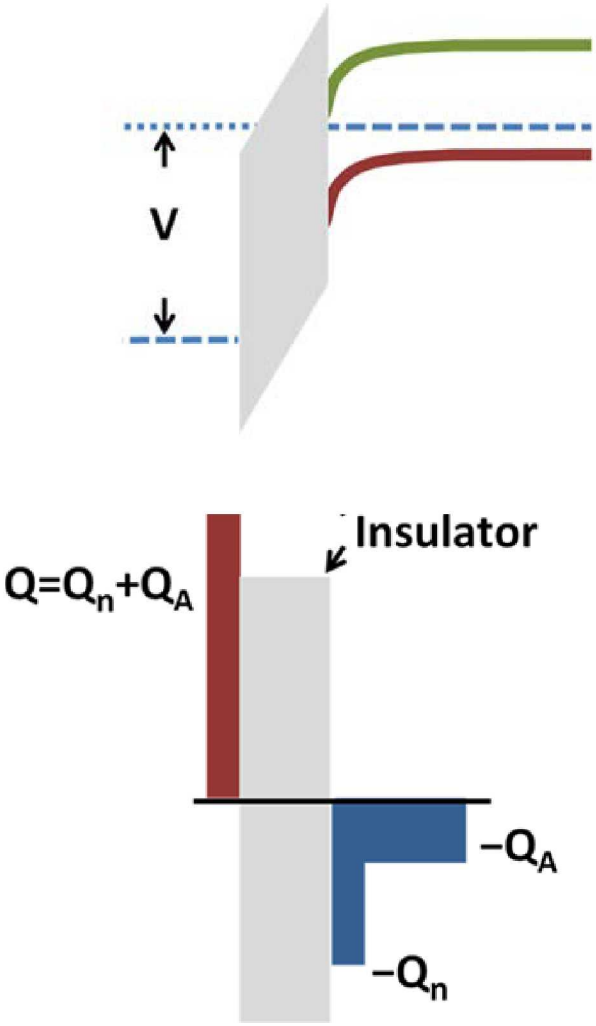

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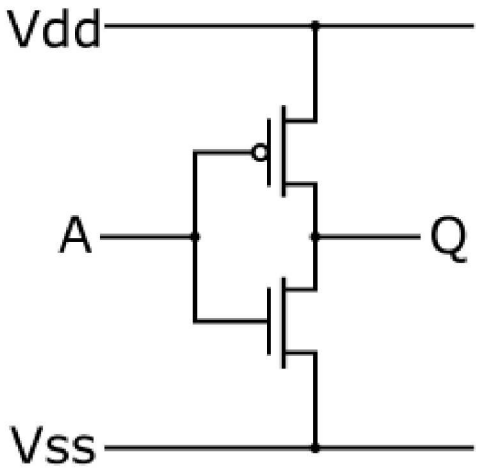

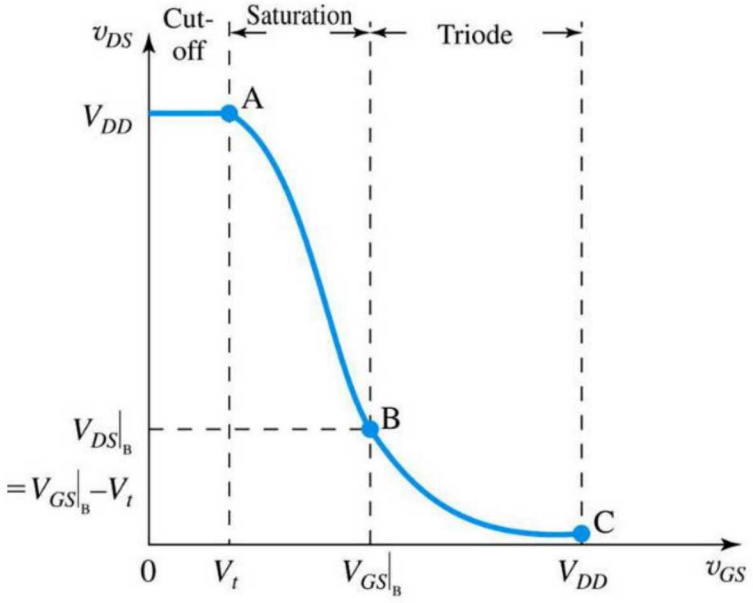

Weak Inversion

$$I_D \approx I_{D0} e^{\frac{\kappa(V_G - V_{th}) - V_S}{V_T}}, \quad \kappa = \frac{C_{ox}}{C_{ox} + C_D}$$

Linear/ Triode

$$I_D = \mu_n C_{ox} \frac{W}{L}\left((V_{GS} - V_{th})V_{DS} - \frac{{V_{DS}}^2}{2}\right)$$

Saturation

$$I_D = \frac{\mu_n C_{ox}}{2}\frac{W}{L}[V_{GS} - V_{th}]^2 [1 + \lambda(V_{DS} - V_{DSsat})]$$

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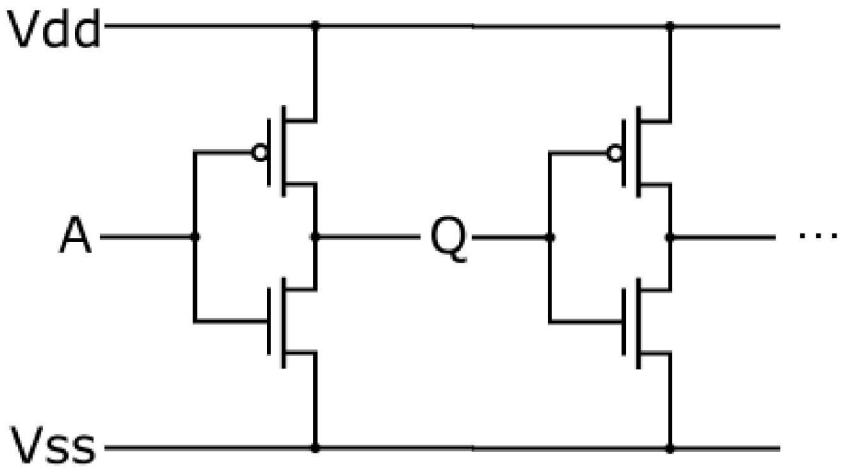

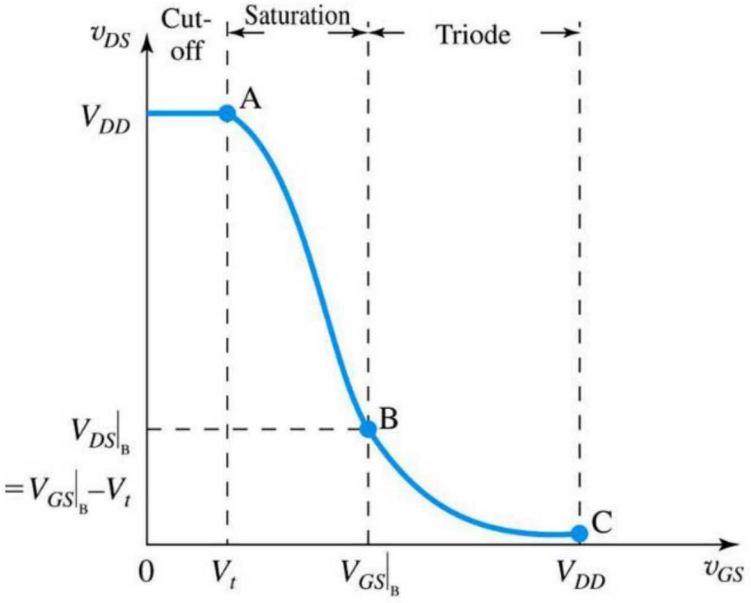

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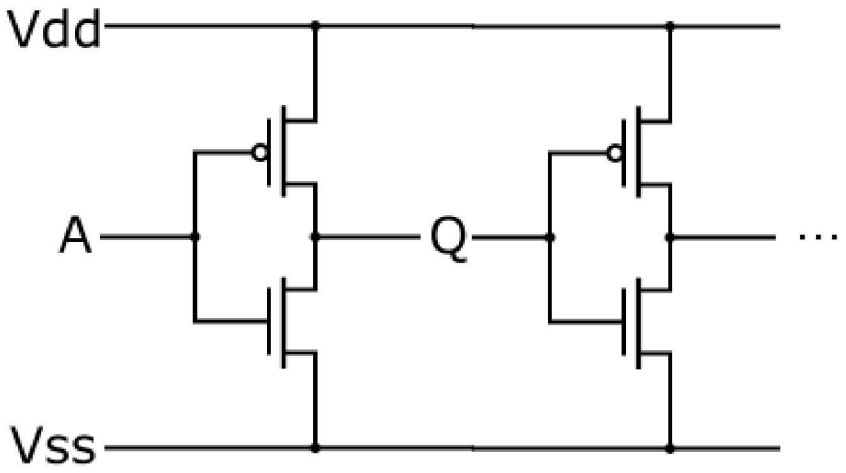
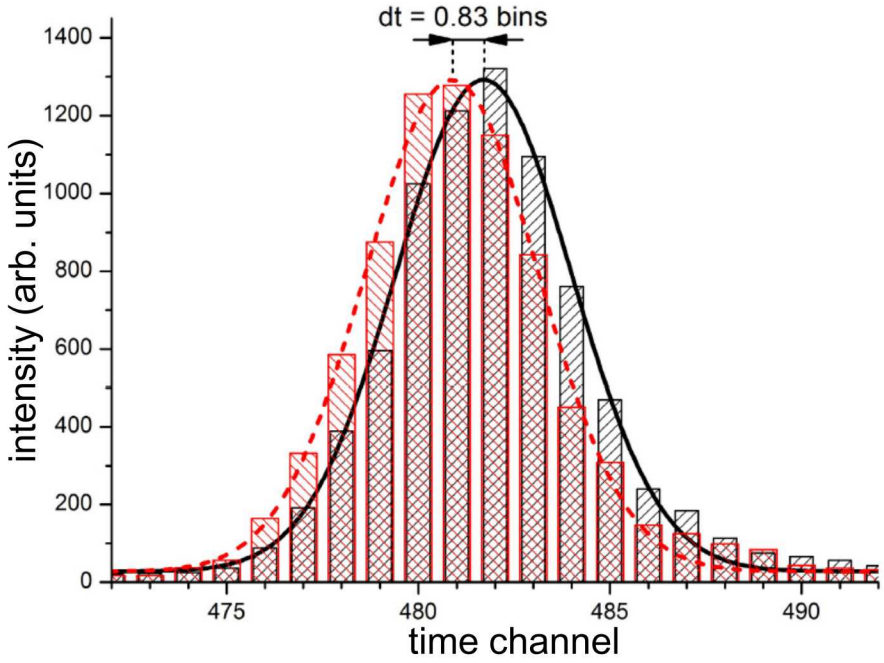




Complex non-linear relationships define propagation delay

~ 1's to 10's picosecond

Very difficult to predict *a priori* (theory/modeling)

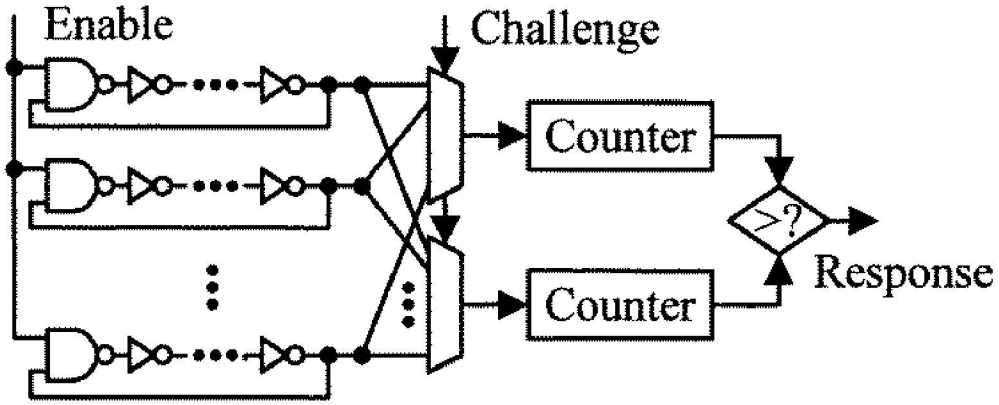
Very difficult to measure *a posteriori* (empirically)

Delay Based PUF

- **Ring Oscillator PUF**

  Based on RO TRNG
  Compares frequency of 2 ROs
  Challenge-Response Pairs (CRPs):

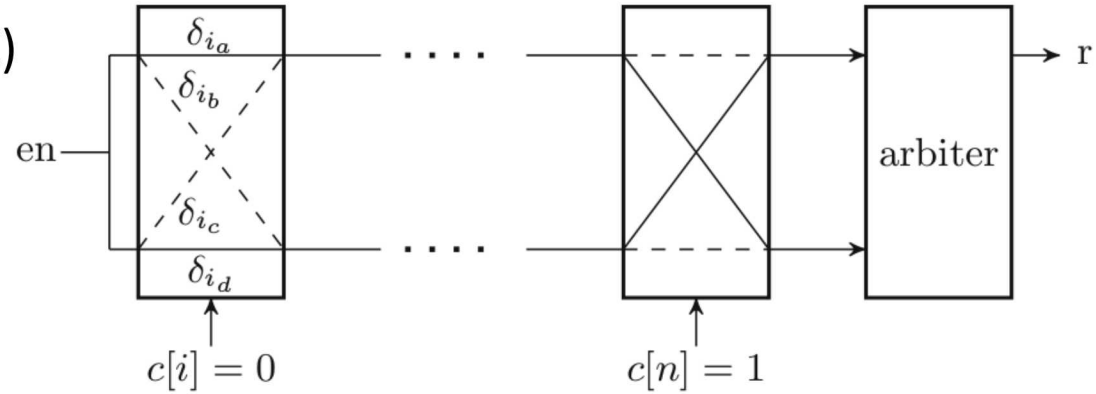
$$\binom{n}{2}$$



- **Arbiter PUF**

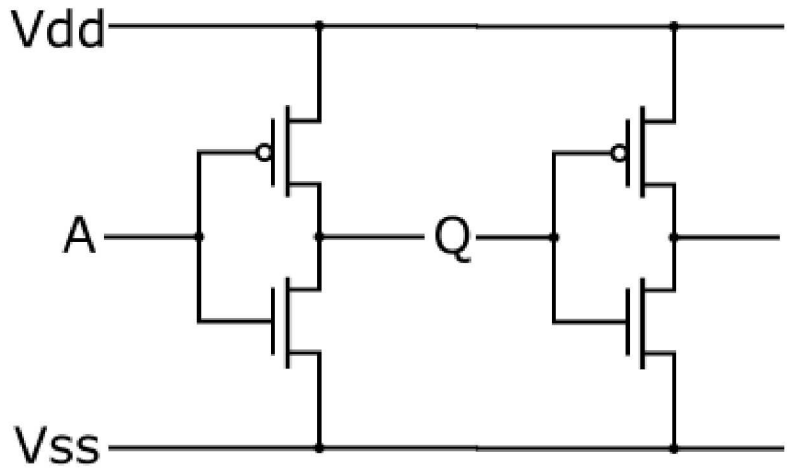
  Element pairwise paths (MUX)
  Race between two nominally identical paths
  Challenge-Response Pairs (CRPs):

$$2^n$$



State Based PUF

- **Static Random Access Memory (SRAM) PUF**



Cross-coupled inverters
Imbalanced transient determines power-on state of cells
Challenge-Response Pairs (CRP): **1**

State Based PUF

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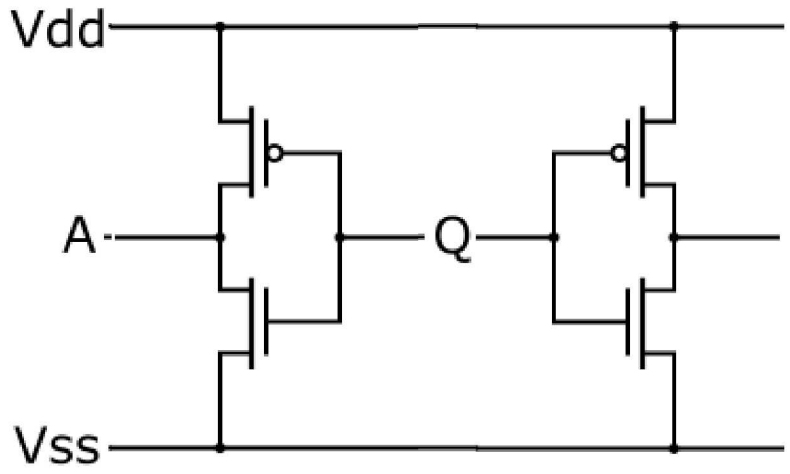

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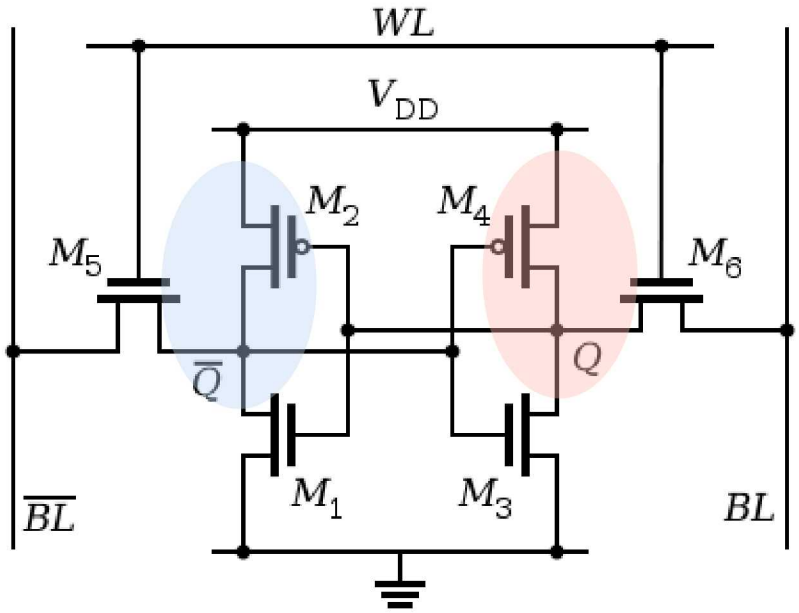

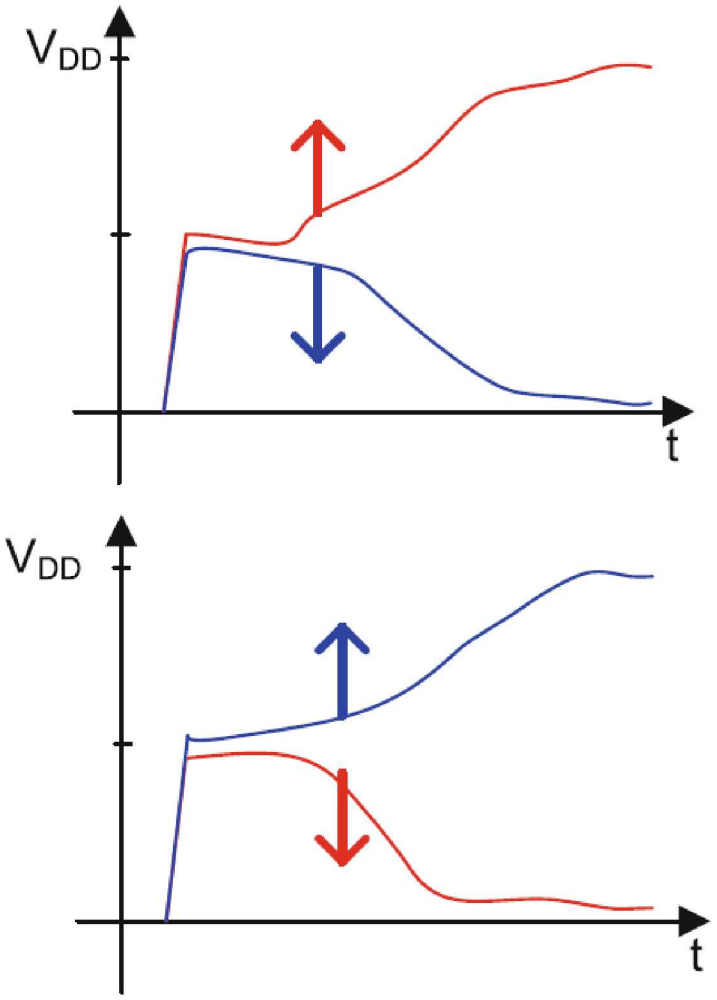

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Challenge-Response Pairs (CRP): **1**

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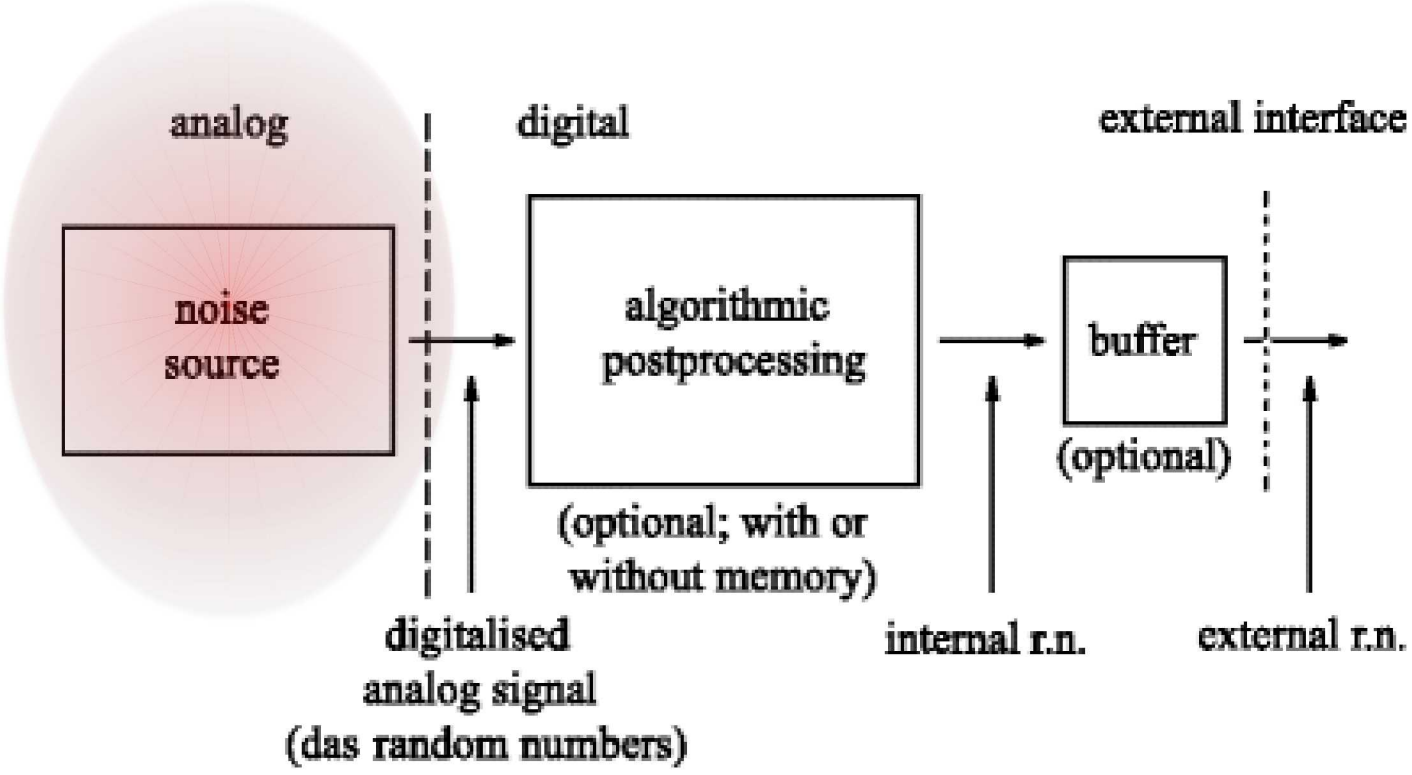
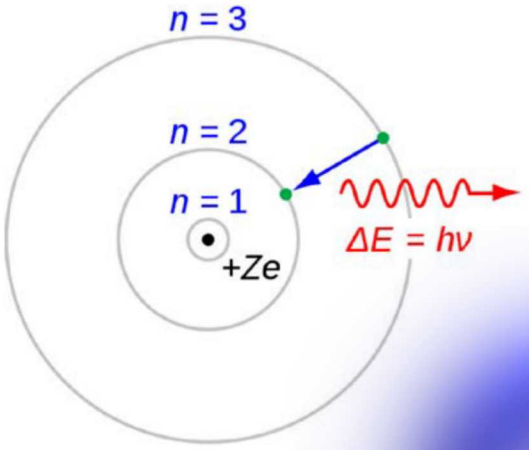


Noise Sources

- Two **fundamental** sources of noise
  - **Quantum mechanics**
    Shot noise

    Single photon detection
    Electrons tunneling
    Nuclear decay



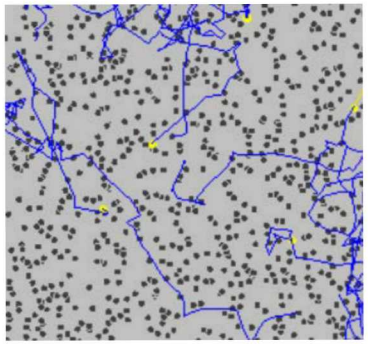
$$\psi_{nlm}(r,\vartheta,\varphi) = \sqrt{\left(\frac{2}{na_0}\right)^3 \frac{(n-l-1)!}{2n[(n+l)!]}} e^{-\rho/2} \rho^l L_{n-l-1}^{2l+1}(\rho) \cdot Y_{lm}(\vartheta,\varphi)$$

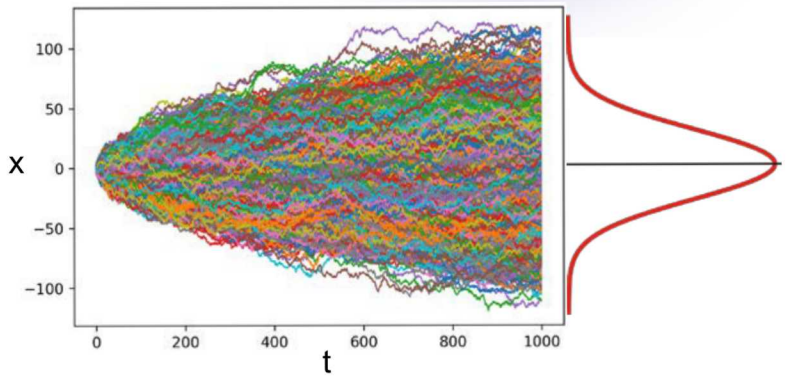
  - **Thermal mechanics**
    Johnson-Nyquist noise

    Thermionic emission
    Avalanche noise
    Atmospheric noise

$$\rho(x,t) = \frac{N}{\sqrt{4\pi D t}} e^{-\frac{x^2}{4Dt}}$$

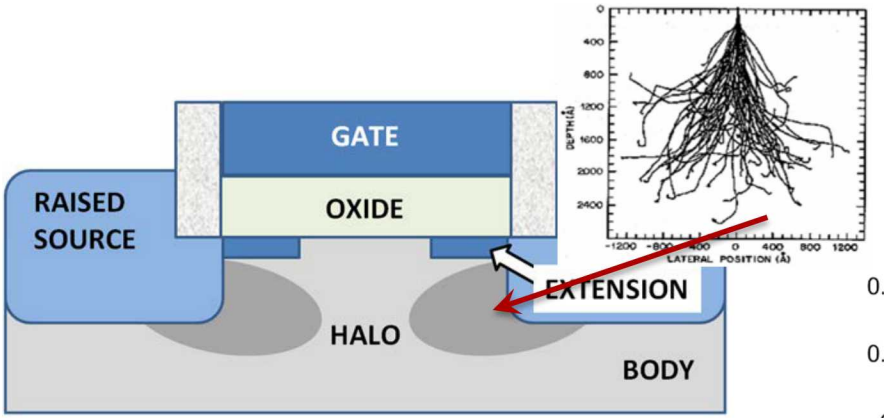
$$D = \mu k_B T$$



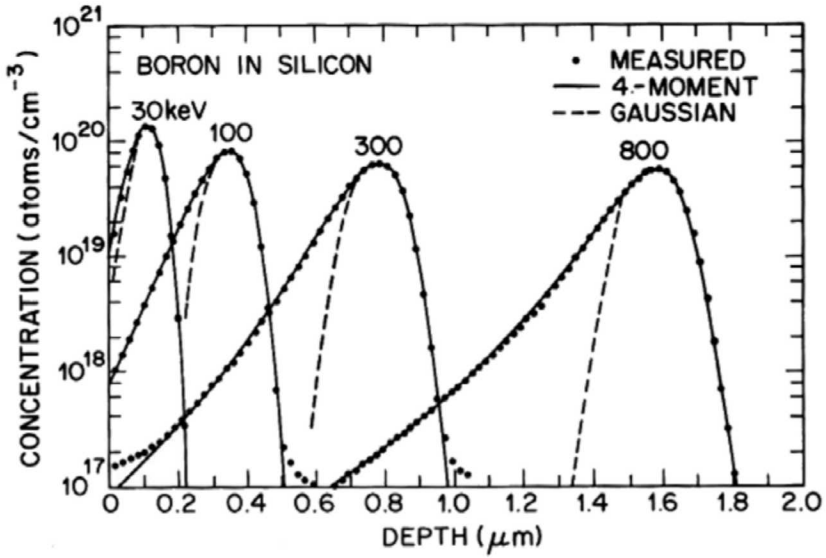


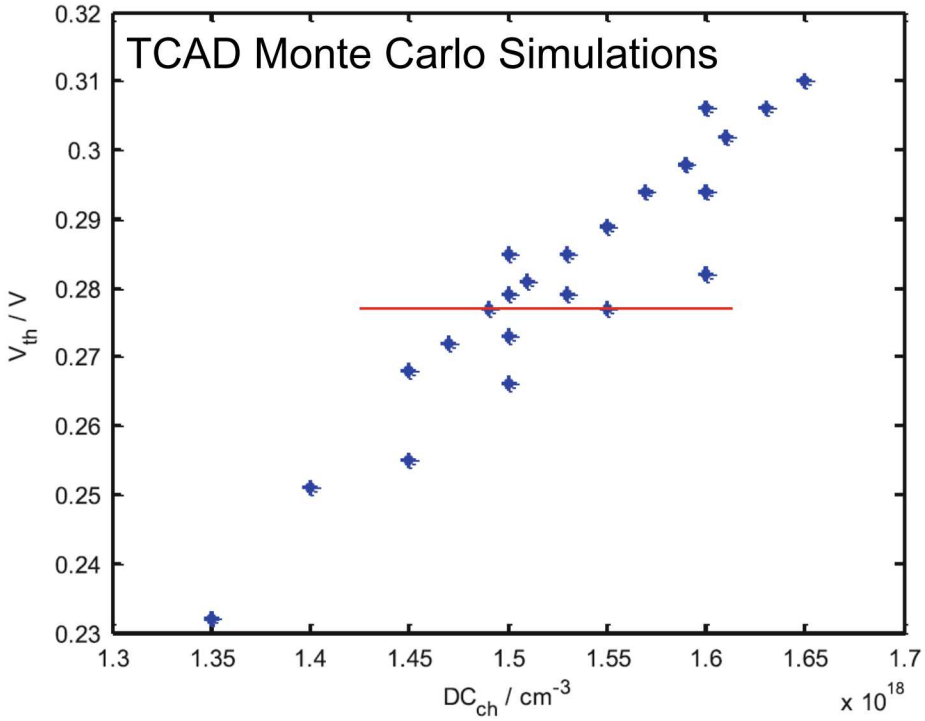
Noise Sources

- "Manufacturing variations" **ARE NOT** fundamental noise sources
  Manufacturing processes **may** contain fundamental noise sources



$$V_{th} \propto \frac{\sqrt{2\epsilon_s q N_a (2\varphi_B + V_{ox})}}{C_{ox}}$$

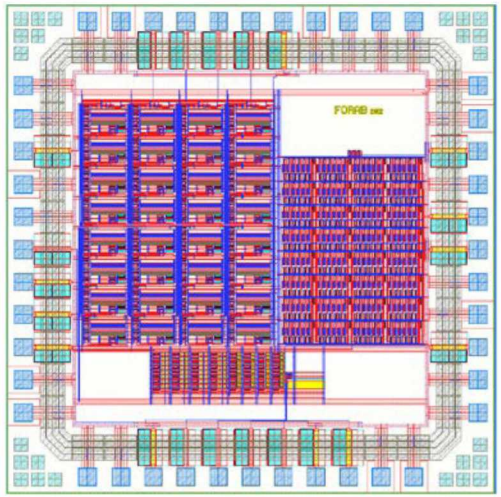


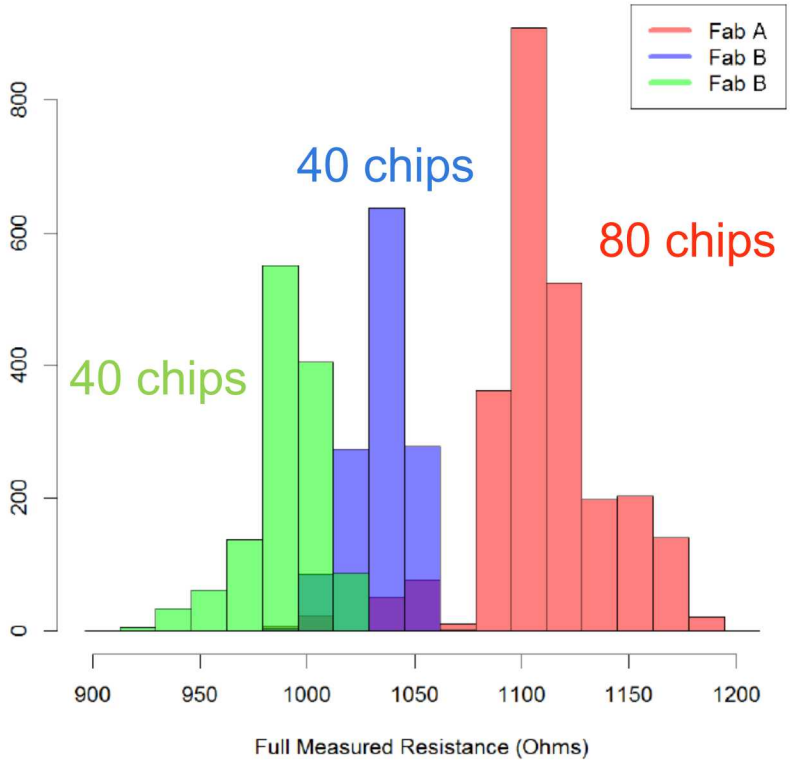


Quality of PUF Noise Sources

- Recall: Keys should be independently, identically distributed (IID)

FORAB chip (350 nm)





  - Resistors: n/p-channel, M1-M4 vias, poly-Si interconnects
  - Capacitors: integrating oscillators
  - Ring oscillators

- Source of randomness is dependent on fab and lot
  Source of randomness is ~ Gaussian distributed
  NOT IID

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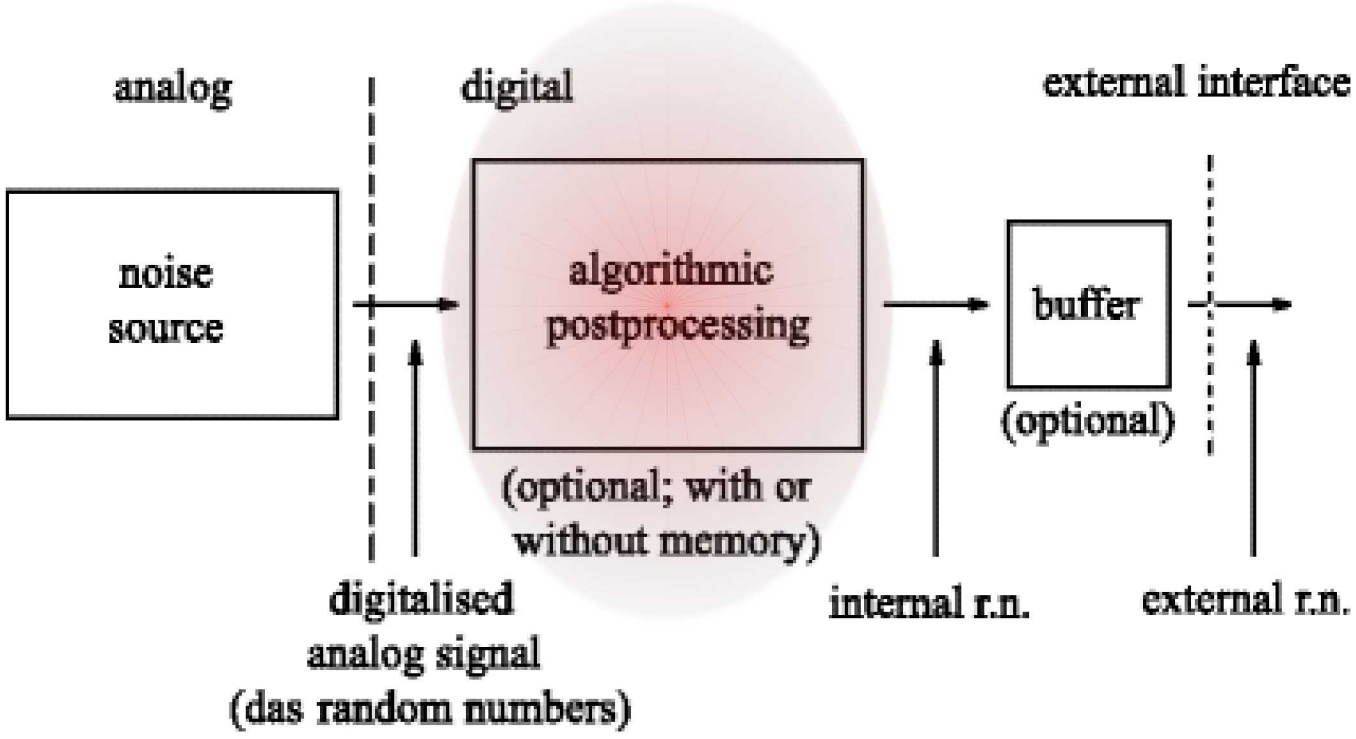
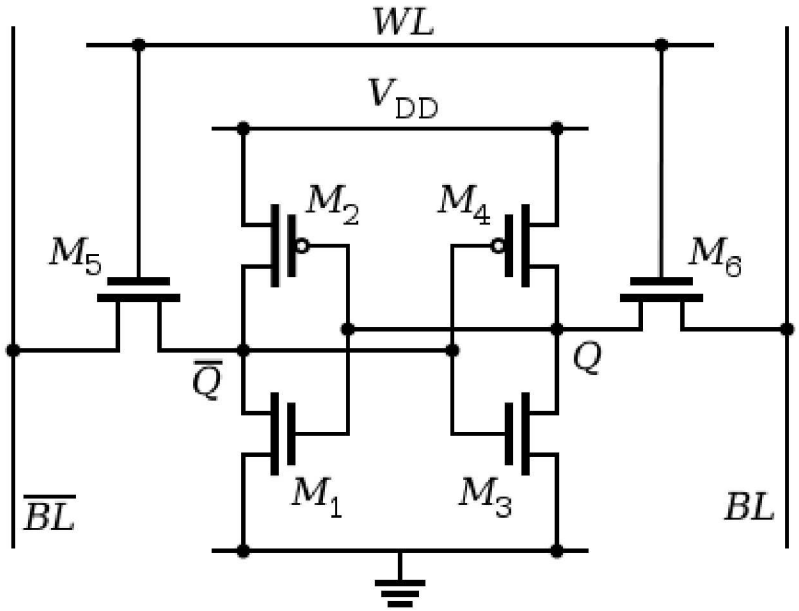
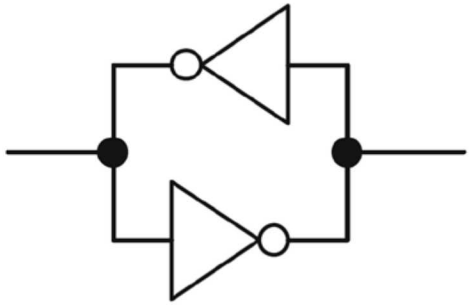


Randomness Extractors

- OK if source is not IID, as long as it's a random variable (**seed**)
  Randomness extractors transform value to IID
  Recall: e.g., SRAM cell is a non-linear feedback circuit





- On power-up, satisfies conditions for an autonomous, chaotic circuit
  1) 1+ non-linear elements
  2) 1+ locally active resistors
  3) 3+ energy storage elements

Randomness Extractors

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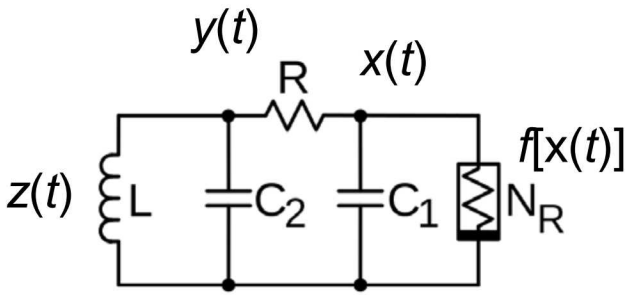
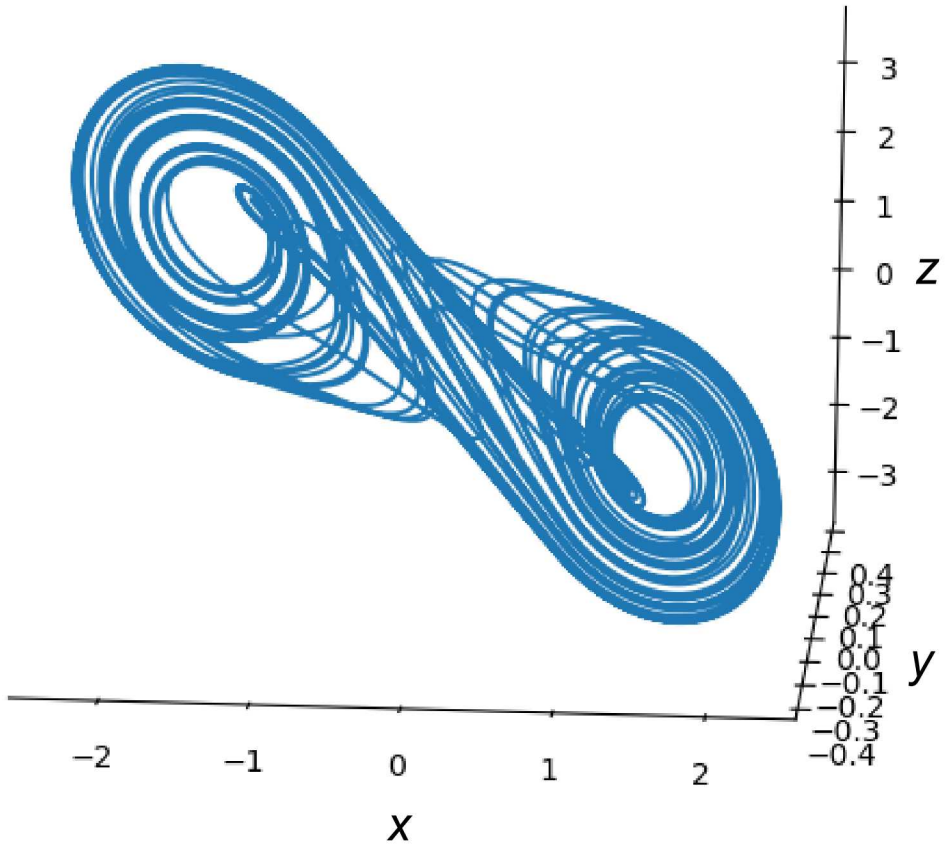
  Randomness extractors transform value to IID
  Chaotic Circuit: Chua's Circuit, a model chaotic circuit



$$\frac{dx}{dt} = \alpha[y - x - f(x)],$$

$$RC_2 \frac{dy}{dt} = x - y + Rz,$$

$$\frac{dz}{dt} = -\beta y.$$



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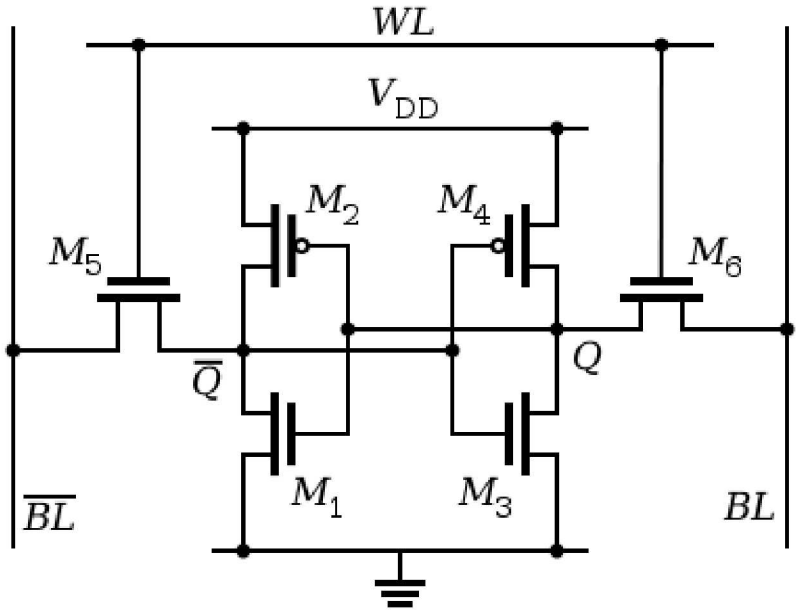
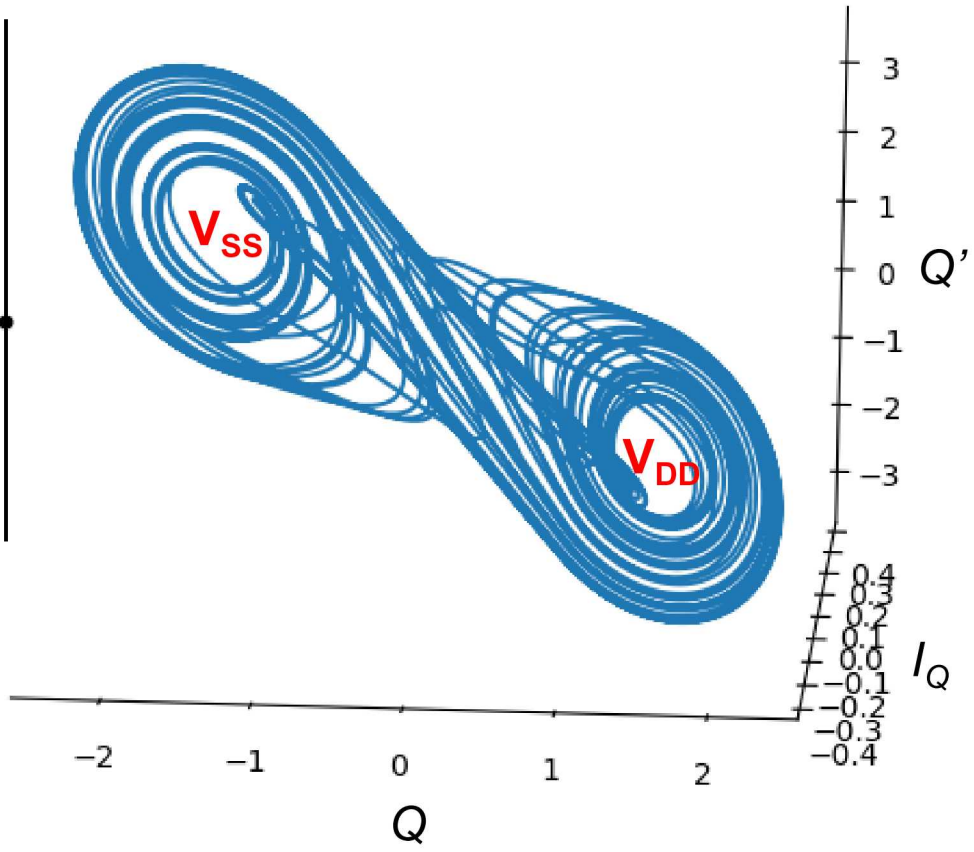
  Chaotic Circuit: SRAM as a chaotic circuit





- Time-dependent output highly sensitive to parameters and starting conditions
  Prone to operational noise

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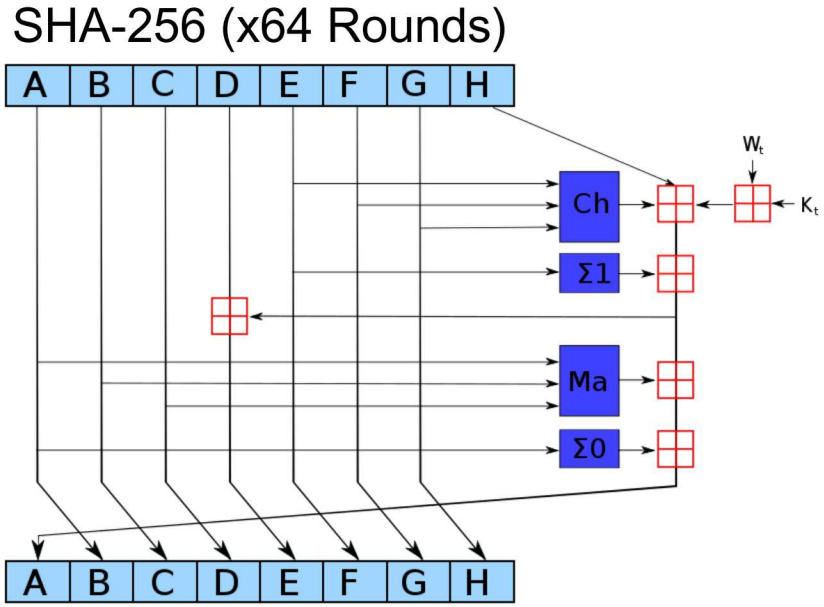
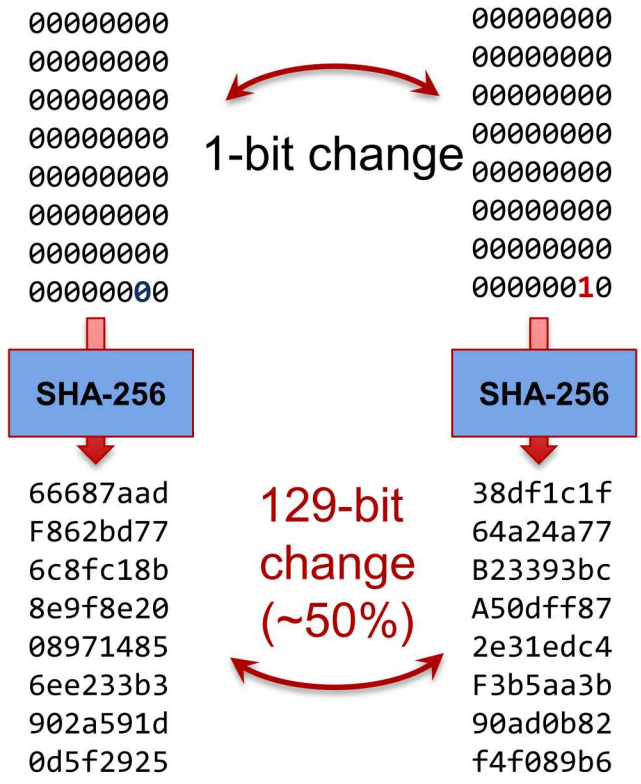
  Randomness extractors transform value to IID
  Algorithmic Extractors: Hash functions, AES S-box



$$\mathrm{Ch}(E,F,G) = (E \wedge F) \oplus (\neg E \wedge G)$$
$$\mathrm{Ma}(A,B,C) = (A \wedge B) \oplus (A \wedge C) \oplus (B \wedge C)$$
$$\Sigma_0(A) = (A \ggg 2) \oplus (A \ggg 13) \oplus (A \ggg 22)$$
$$\Sigma_1(E) = (E \ggg 6) \oplus (E \ggg 11) \oplus (E \ggg 25)$$

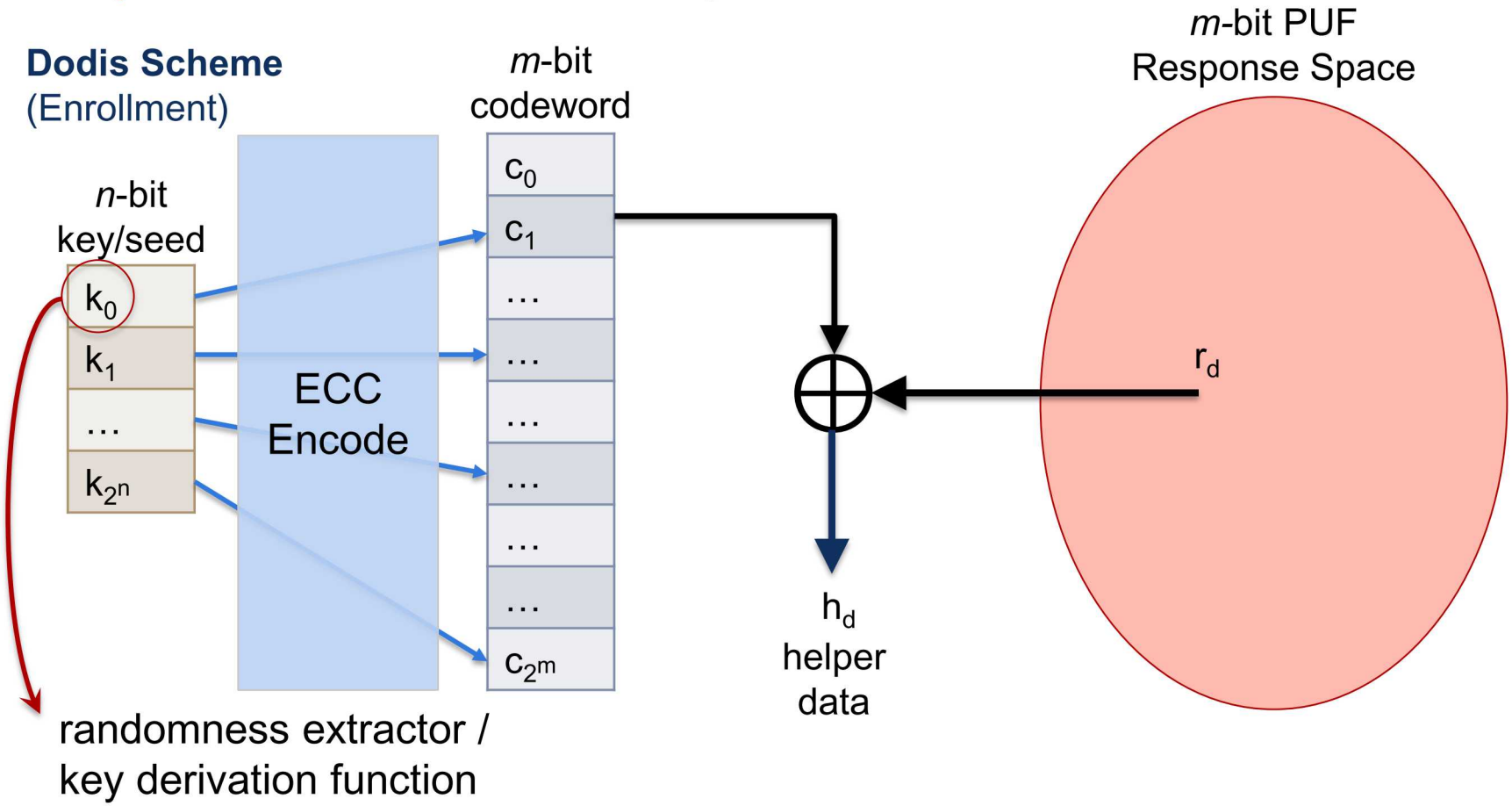


- Hashes designed to amplify changes in input: **Prone to operational noise**

Fuzzy Extractors

- Randomness extractors sensitive to operational noise

  Fuzzy extractors add some reliability back



Fuzzy Extractors

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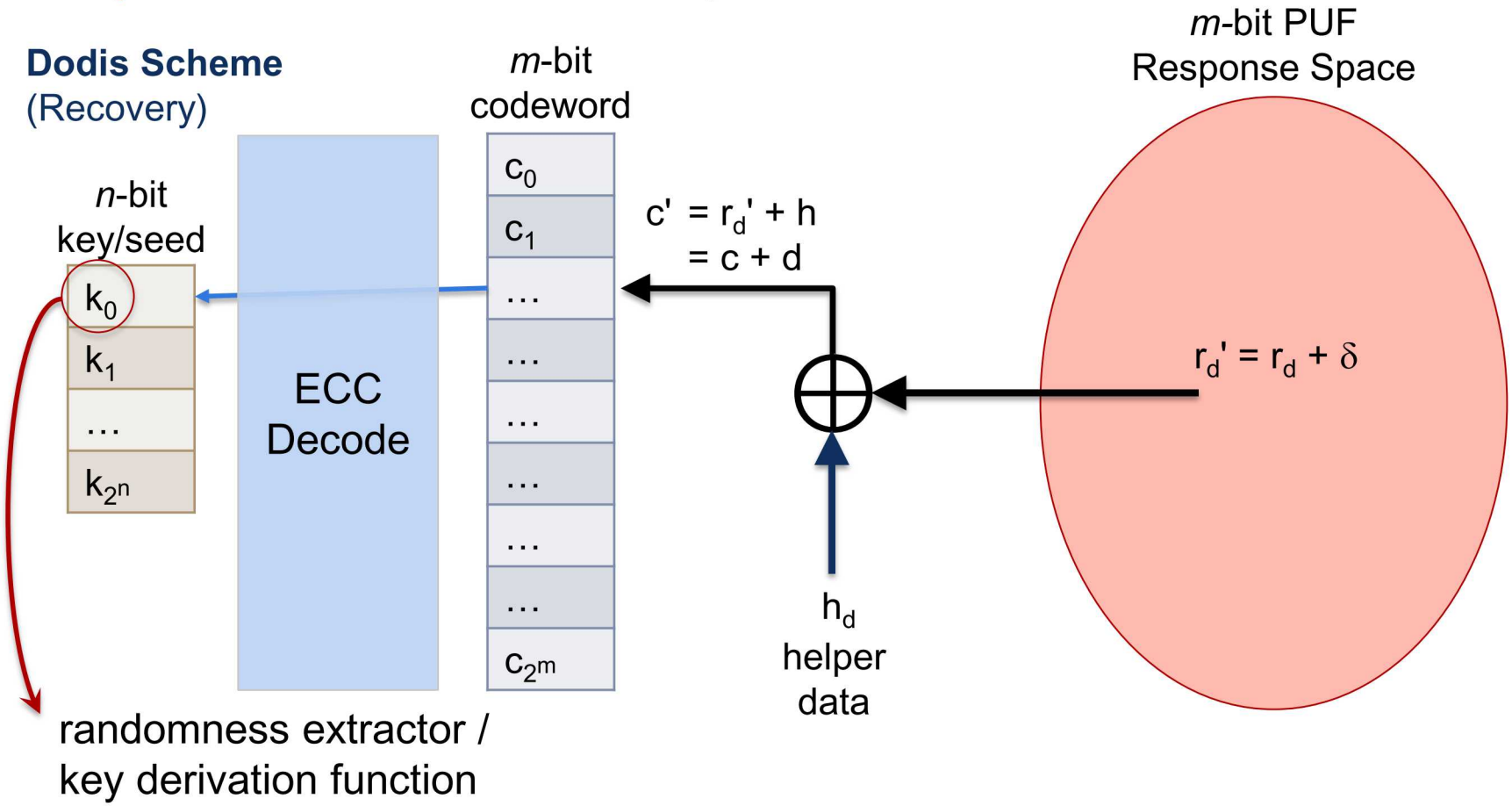
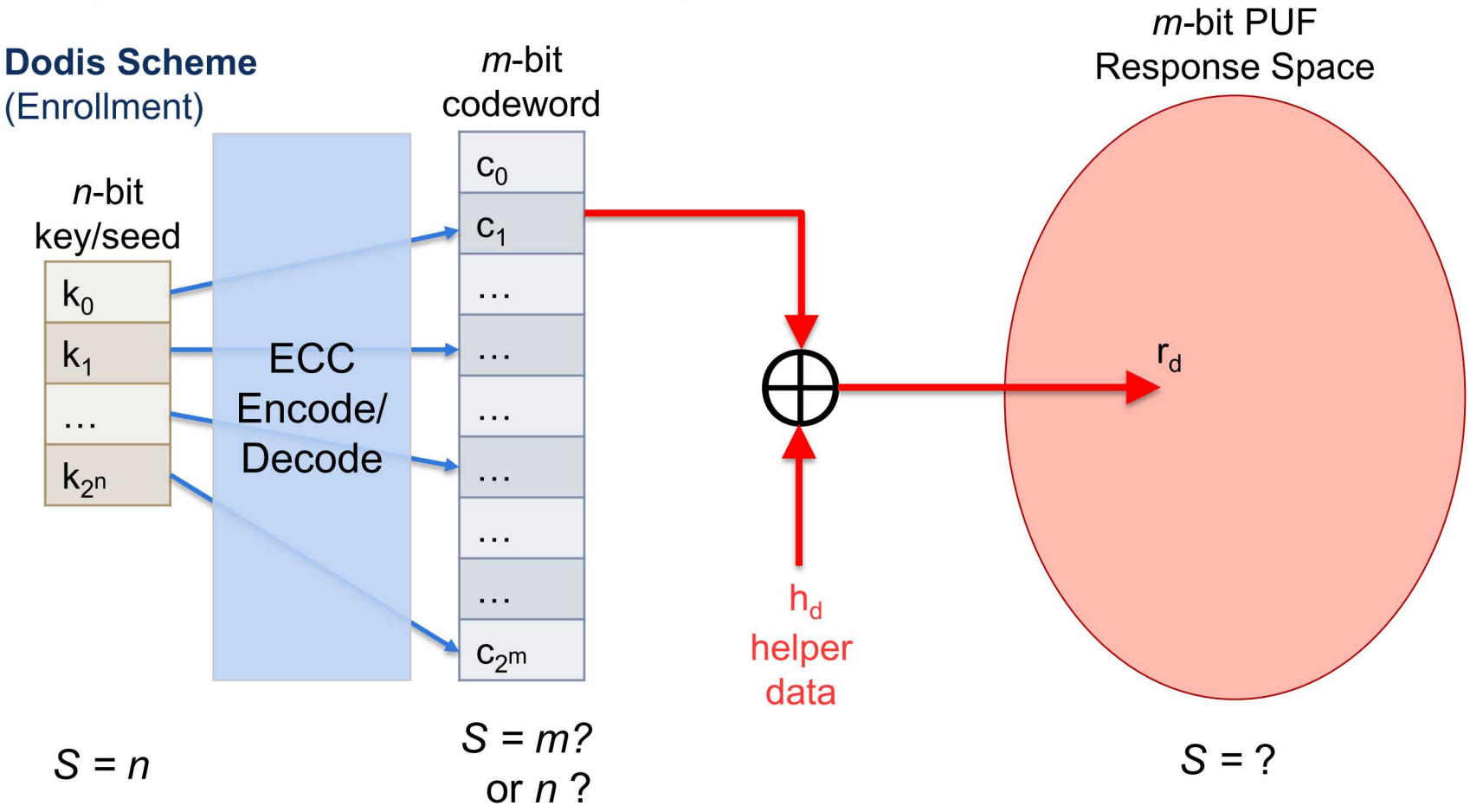


- **PUFs serve as a device-specific one-time pad, hiding sensitive information**

Fuzzy Extractors

- Randomness extractors sensitive to operational noise

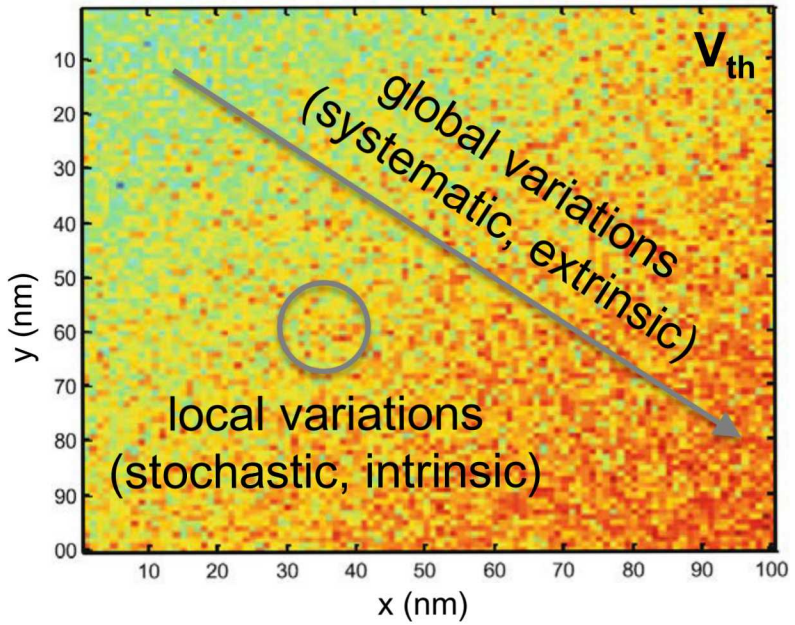
  Fuzzy extractors add some reliability back

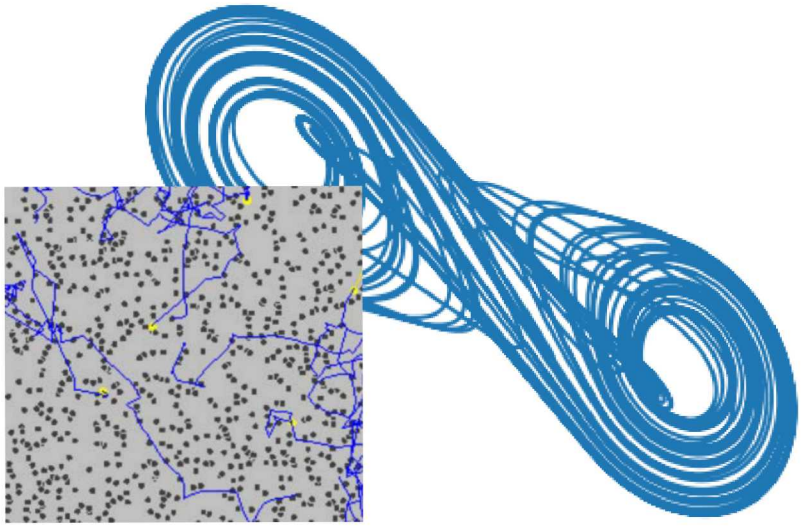


- **Caution: Scheme only as secure as your least entropic element (PUF?)**

Summary

- PUFs leverage manufacturing variations in ICs as digital fingerprints for keys or seeds.
- "PUFs are now a secure alternative [for] secret keys…" (Wikipedia)





- PUFs are likely stochastic and chaotic, but exact sources and distributions TBD.
- PUFs should be implemented and used with extreme care.